

## Silicon Standard Recovery Diode

$V_{RRM} = 100\text{ V} - 1200\text{ V}$   
 $I_F = 6\text{ A}$

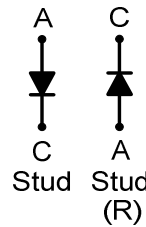
### Features

- High Surge Capability
- Types up to 1200 V  $V_{RRM}$

DO-4 Package

### Note:

1. Standard polarity: Stud is cathode.
2. Reverse polarity (R): Stud is anode.
3. Stud is base.



### Maximum ratings, at $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	S6B (R)	S6D (R)	S6G (R)	S6J (R)	Unit
Repetitive peak reverse voltage	$V_{RRM}$		100	200	400	600	V
RMS reverse voltage	$V_{RMS}$		70	140	280	420	V
DC blocking voltage	$V_{DC}$		100	200	400	600	V
Continuous forward current	$I_F$	$T_C \leq 160\text{ }^\circ\text{C}$	6	6	6	6	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ }^\circ\text{C}$ , $t_p = 8.3\text{ ms}$	167	167	167	167	A
Operating temperature	$T_j$		-65 to 175	-65 to 175	-65 to 175	-65 to 175	$^\circ\text{C}$
Storage temperature	$T_{stg}$		-65 to 200	-65 to 200	-65 to 200	-65 to 200	$^\circ\text{C}$

### Electrical characteristics, at $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	S6B (R)	S6D (R)	S6G (R)	S6J (R)	Unit
Diode forward voltage	$V_F$	$I_F = 6\text{ A}$ , $T_j = 25\text{ }^\circ\text{C}$	1.1	1.1	1.1	1.1	V
Reverse current	$I_R$	$V_R = 100\text{ V}$ , $T_j = 25\text{ }^\circ\text{C}$	10	10	10	10	$\mu\text{A}$
		$V_R = 100\text{ V}$ , $T_j = 175\text{ }^\circ\text{C}$	12	12	12	12	mA

### Thermal characteristics

Thermal resistance, junction - case	$R_{thJC}$		2.50	2.50	2.50	2.50	$^\circ\text{C/W}$
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Figure .1-Typical Forward Characteristics

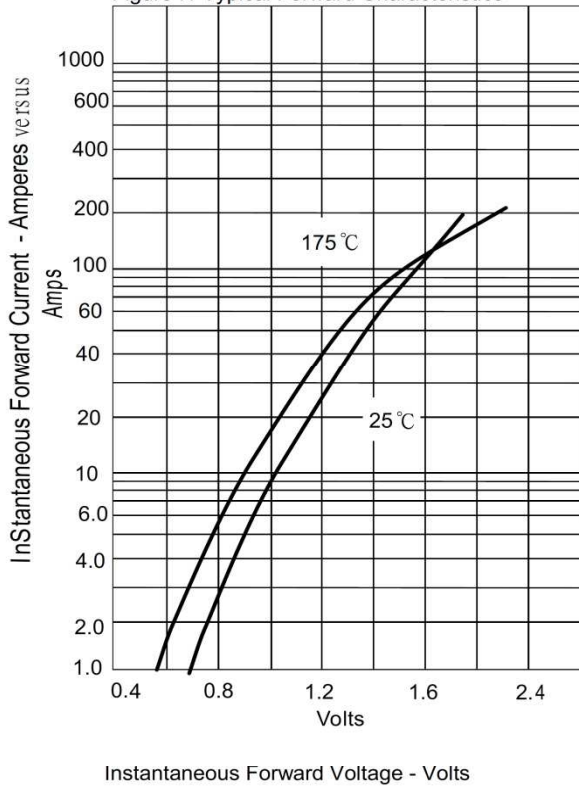


Figure .2-Forward Derating Curve

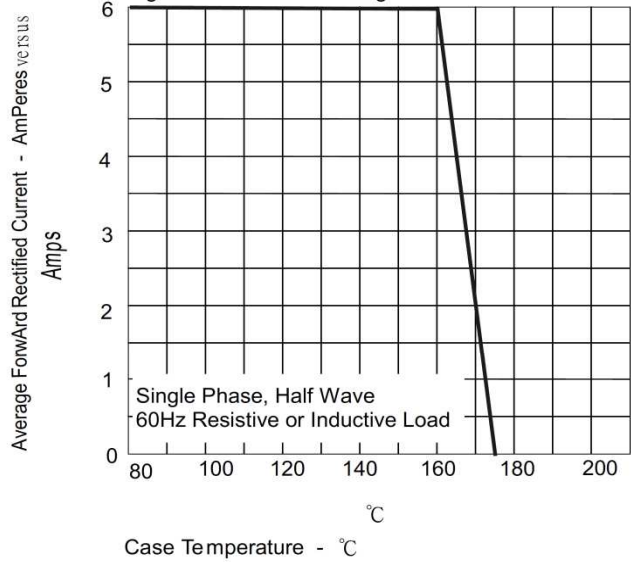


Figure .3-Peak Forward Surge Current

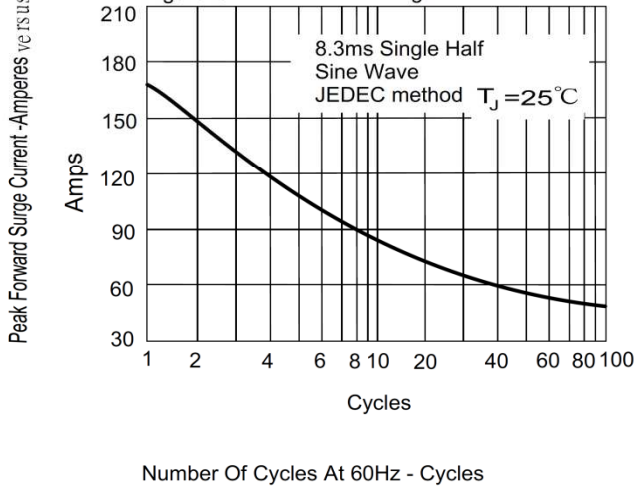


Figure .4-Typical Reverse Characteristics

